

Silicon PNP Power Transistors

2SB695

DESCRIPTION

- With TO-3PN package
- Wide area of safe operation

APPLICATIONS

- For power amplifier and general purpose applications

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Base |
| 2 | Collector;connected to mounting base |
| 3 | Emitter |

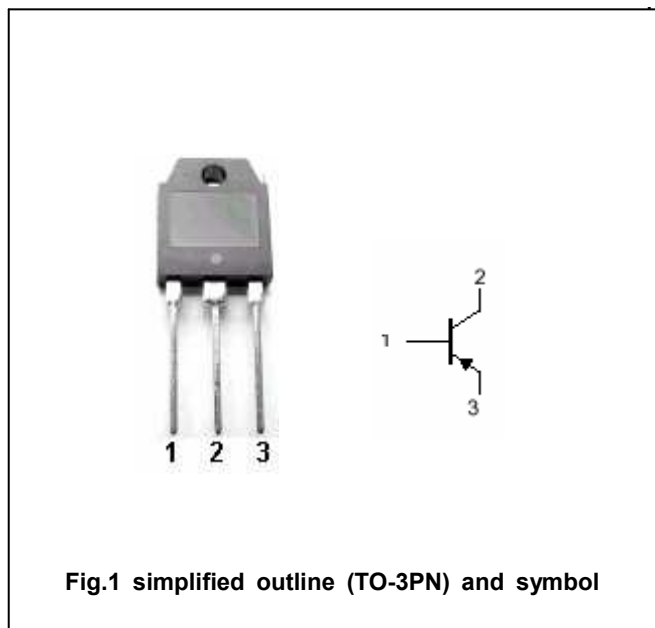


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings($T_c=25^\circ\text{C}$)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|-----------------------------|------------------------|---------|------------------|
| V_{CBO} | Collector-base voltage | Open emitter | -170 | V |
| V_{CEO} | Collector-emitter voltage | Open base | -120 | V |
| V_{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I_C | Collector current | | -7 | A |
| P_C | Collector power dissipation | $T_c=25^\circ\text{C}$ | 80 | W |
| T_j | Junction temperature | | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | | -55~150 | $^\circ\text{C}$ |

Silicon PNP Power Transistors

2SB695

CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|------|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-30mA ; I _B =0 | -120 | | | V |
| V _{(BR)CBO} | Collector-base breakdown voltage | I _C =-1mA ; I _E =0 | -170 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =-1mA ; I _C =0 | -5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-5A; I _B =-0.5A | | | -1.5 | V |
| V _{BE} | Base-emitter on voltage | I _C =-1A; V _{CE} =-5V | | | -1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-170V; I _E =0 | | | -50 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =-5V; I _C =0 | | | -50 | μA |
| h _{FE-1} | DC current gain | I _C =-1A ; V _{CE} =-5V | 40 | | 200 | |
| h _{FE-2} | DC current gain | I _C =-5A ; V _{CE} =-5V | 20 | | | |
| f _T | Transition frequency | I _C =-1A ; V _{CE} =-5V | | 7 | | MHz |

Silicon PNP Power Transistors

2SB695

PACKAGE OUTLINE

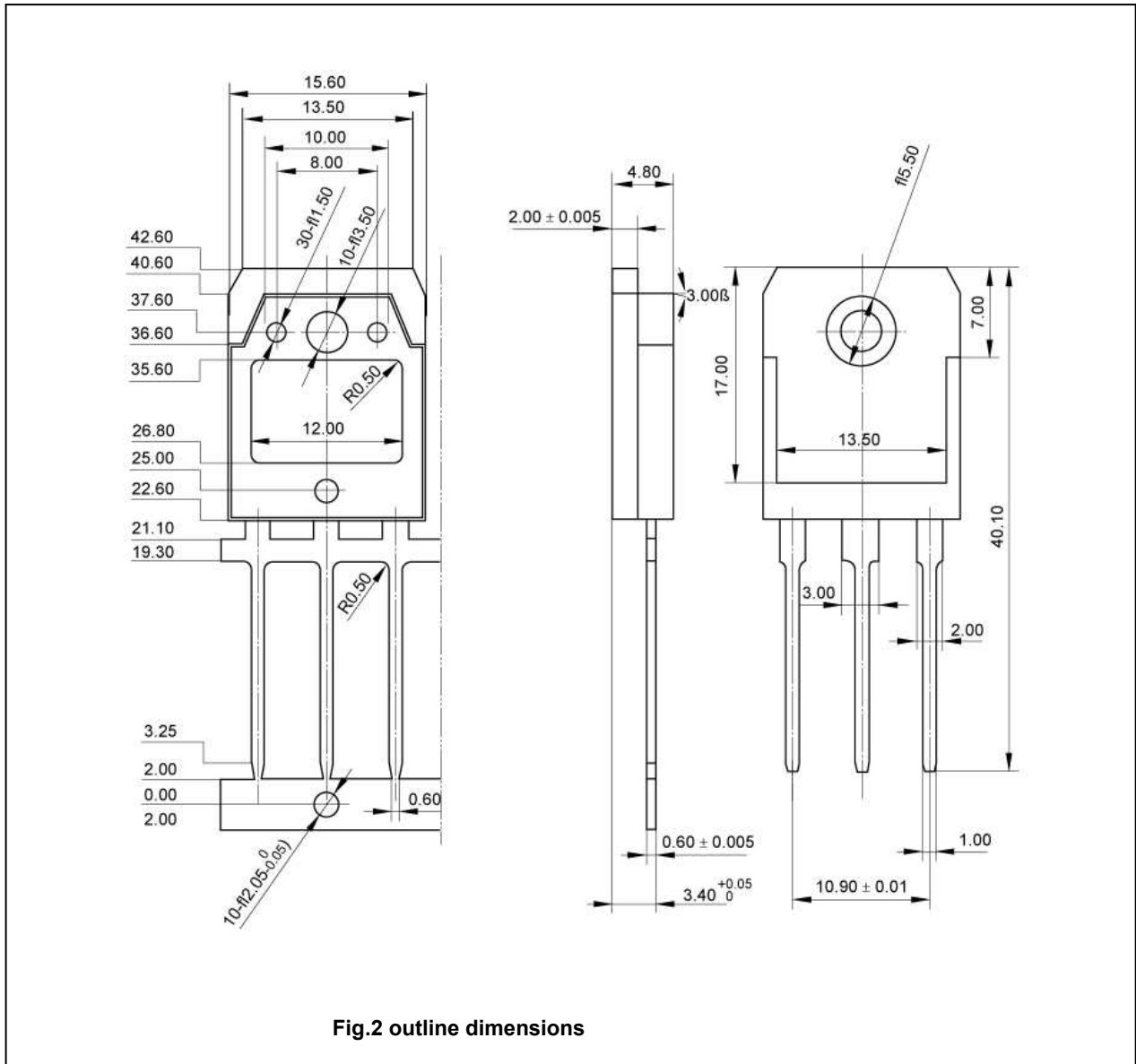


Fig.2 outline dimensions